

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (DARLINGTON POWER)

# 2SB1067

MICRO MOTER DRIVE, HAMMER DRIVE APPLICATIONS.  
SWITCHING APPLICATIONS.  
POWER AMPLIFIER APPLICATIONS.

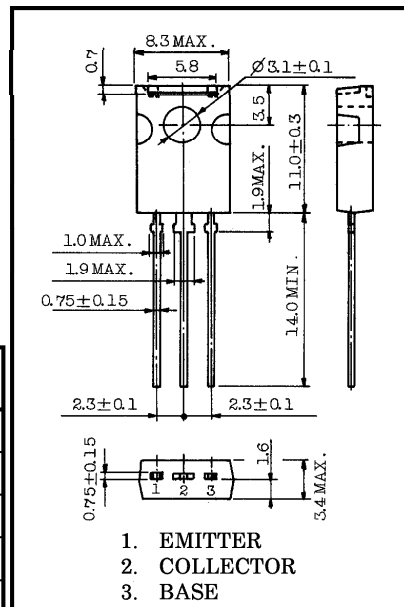
INDUSTRIAL APPLICATIONS

Unit in mm

- High DC Current Gain  
:  $h_{FE} = 2000$  (Min.) ( $V_{CE} = -2V$ ,  $I_C = -1A$ )
- Low Saturation Voltage  
:  $V_{CE(sat)} = -1.5V$  (Max.) ( $I_C = -1A$ ,  $I_B = -1mA$ )

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

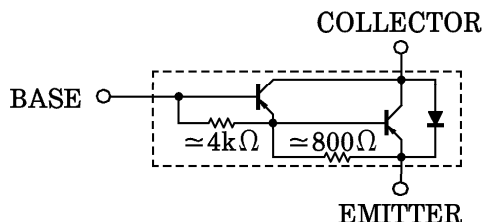
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-80	V
Collector-Emitter Voltage	$V_{CEO}$	-80	V
Emitter-Base Voltage	$V_{EBO}$	-8	V
Collector Current	$I_C$	-2	A
Base Current	$I_B$	-0.5	A
Collector Power Dissipation	$P_C$	$T_a = 25^\circ C$	1.5
		$T_c = 25^\circ C$	10
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ C$



JEDEC	—
EIAJ	—
TOSHIBA	2-8H1A

Weight : 0.82g

EQUIVALENT CIRCUIT



961001EAA2

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		$I_{CBO}$	$V_{CB} = -80V, I_E = 0$	—	—	-10	$\mu A$
Emitter Cut-off Current		$I_{EBO}$	$V_{EB} = -8V, I_C = 0$	—	—	-4	mA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-80	—	—	V
DC Current Gain		$h_{FE}$	$V_{CE} = -2V, I_C = -1A$	2000	—	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = -1A, I_B = -1mA$	—	—	-1.5	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = -1A, I_B = -1mA$	—	—	-2.0	V
Transition Frequency		$f_T$	$V_{CE} = -2V, I_C = -0.5A$	—	50	—	MHz
Collector Output Capacitance		$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	30	—	pF
Switching Time	Turn-on Time	$t_{on}$	<p><math>I_{B1} = I_{B2} = 1mA</math> DUTY CYCLE <math>\leq 1\%</math> <math>V_{CC} = -30V</math></p>	—	0.4	—	$\mu s$
	Storage Time	$t_{stg}$		—	2.0	—	
	Fall Time	$t_f$		—	0.4	—	

